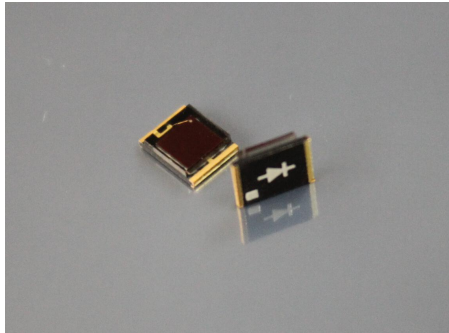


## Visible light enhanced photodiode



## Description

The OSD9-HM is device as visible, IR wavelength photodiode in COB package, It can get fast response output of high Sensitivity for visible light. This device is ideal for applications Such as smartwatch, smartphone, smart bracelet etc.

## Features

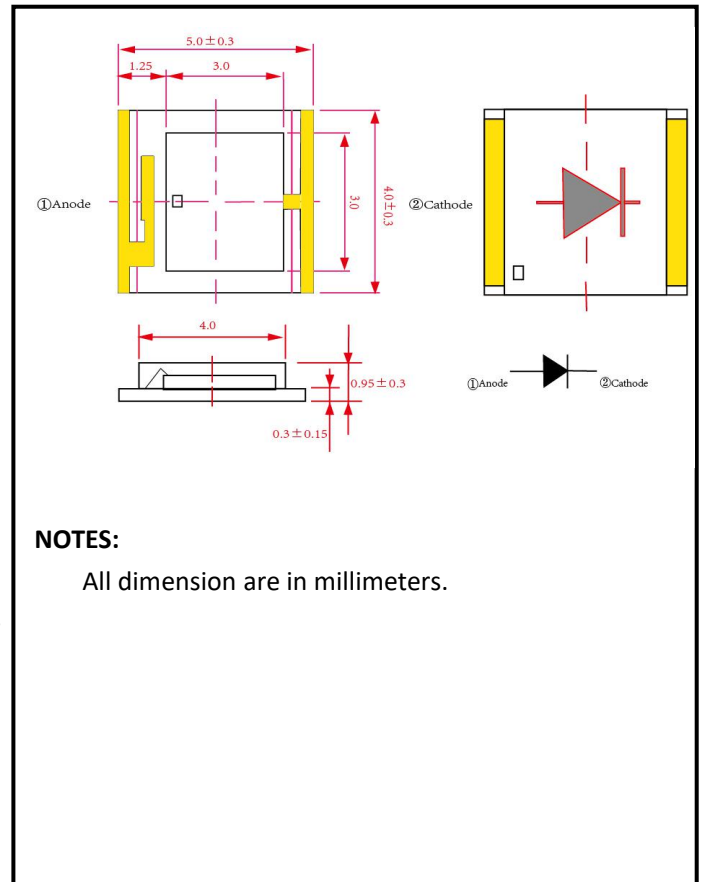
- \* high sensitivity for visible light.
- \* Low dark current
- \* Operating temperature is from  $-40$  to  $+80^{\circ}\text{C}$
- \* Storage temperature is from  $-40$  to  $+100^{\circ}\text{C}$

## General Ratings

- \* peak wavelength: 940nm
- \* Low capacitance

## Applications

- \* Optical switch
- \* Medical
- \* AR, VR, Wearable



### NOTES:

All dimension are in millimeters.

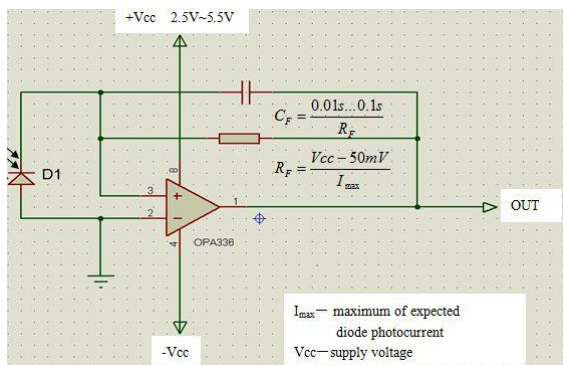
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## Absolute Maximum Ratings (Ta=25°C)

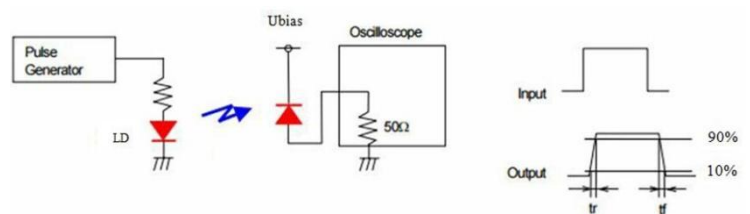
| Parameter                          | Symbol             | Condition  | Min. | Typ.                   | Max. | Unit                    |
|------------------------------------|--------------------|--|------|------------------------|------|-------------------------|
| Chip size                          | Size               |  |      | 3.0*3.0                |      | mm <sup>2</sup>         |
| Active area                        | A                  |  |      | 2.84*2.84              |      | mm <sup>2</sup>         |
| Short circuit Current              | I <sub>sc</sub>    | V <sub>r</sub> =5V, E <sub>v</sub> =5mw/cm <sup>2</sup> f <sub>c</sub> =2856k* |      | 95                     |      | μA                      |
| Isc Temperature Coefficient        | TC I <sub>sc</sub> | 2856k  |      | 1.1                    |      | %/°C                    |
| Open Circuit Voltage               | V <sub>oc</sub>    | V <sub>r</sub> =5V, E <sub>v</sub> =5mw/cm <sup>2</sup> f <sub>c</sub> =2856k* |      | 380                    |      | mV                      |
| Voc Temperature Coefficient        | TC Voc             | 2856k  |      | -2.2                   |      | mV/°C                   |
| Dark current                       | I <sub>d</sub>     | V <sub>R</sub> =100mV  |      | 15                     |      | pA                      |
|                                    |                    | V <sub>R</sub> =10V  |      | 25                     |      |                         |
| Rise time                          | t <sub>r**</sub>   | V <sub>R</sub> =0V; λ=635nm; R <sub>L</sub> =50Ω, f=1KHz                       |      | 100                    |      | ns                      |
|                                    |                    | V <sub>R</sub> =10V; λ=635nm; R <sub>L</sub> =50Ω, f=1KHz                      |      | 80                     |      | ns                      |
| Temp coefficient of I <sub>d</sub> | T <sub>CID</sub>   |  |      | 0.18                   |      | times/°C                |
| Reverse breakdown voltage          | V <sub>(BR)R</sub> | I <sub>R</sub> =100μA E <sub>v</sub> =0lx                                      | 40   |                        |      | V                       |
| Junction Capacitance               | C <sub>J</sub>     | V <sub>R</sub> =0V f=1MHz  |      | 70                     |      | pF                      |
|                                    |                    | V <sub>R</sub> =10V f=1MHz   |      | 25                     |      |                         |
| Photo sensitivity                  | S <sub>R</sub>     | 650nm  |      | 0.42                   |      | A/W                     |
|                                    |                    | 940nm  |      | 0.64                   |      |                         |
| Spectral Application Range         | λ <sub>range</sub> |  | 400  |                        | 1100 | nm                      |
| Spectral Response-Peak             | λ <sub>p</sub>     |  |      | 940                    |      | nm                      |
| Shunt resistance                   | R <sub>sh</sub>    | V <sub>R</sub> =10mV   |      | 0.5                    |      | GΩ                      |
| Rsh Temperature Coefficient        | TC R <sub>sh</sub> | E <sub>v</sub> =100lx, V <sub>R</sub> =10mV                                    |      | 0.18                   |      | %/°C                    |
| Angular Resp 50% Resp Pt           | θ <sub>1/2</sub>   |  |      | ±30                    |      | Degrees                 |
| Noise Equivalent Power             | NEP                | V <sub>R</sub> =10V λ=940nm  |      | 2.58×10 <sup>-14</sup> |      | W/Hz <sup>1/2</sup>     |
| Specific Detectivity               | D*                 | V <sub>R</sub> =10V λ=940nm  |      | 1.67×10 <sup>13</sup>  |      | cm(Hz/W) <sup>1/2</sup> |

\* E<sub>v</sub>: Illuminance by CIE standard light source A (tungsten lamp)

### ■ Typical application circuit



### \*\* Response time measurement Circuit:



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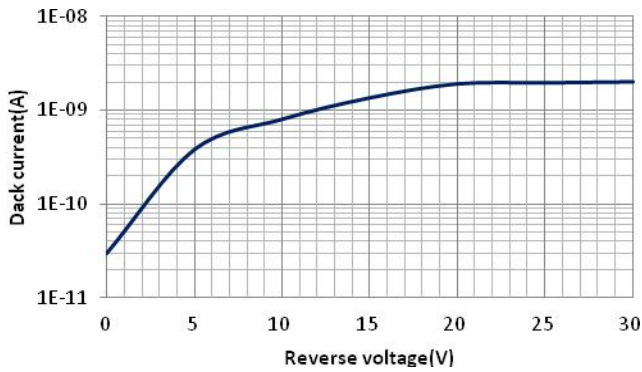
TEL:+86-21-54971821

FAX:+86-21-54971823

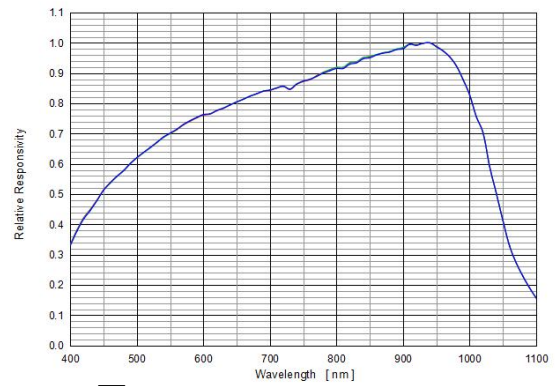
EMAIL: frank.shuai@e-otron.com

<http://www.e-otron.com>

## Dark current vs. reverse voltage

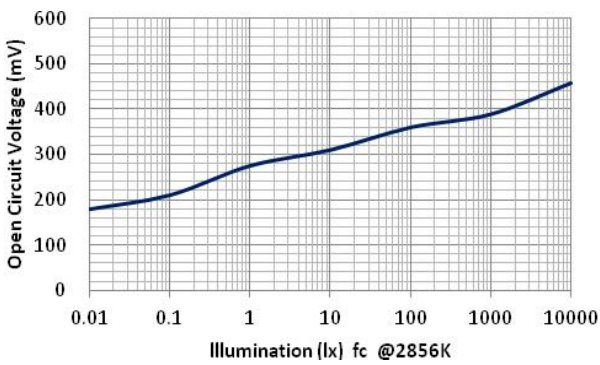


## Spectral response



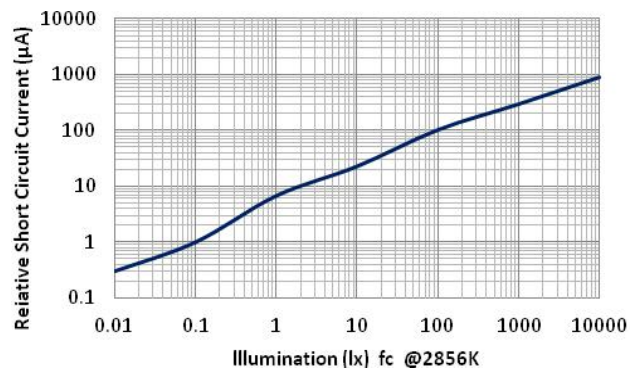
## Open circuit Voltage

vs Illumination



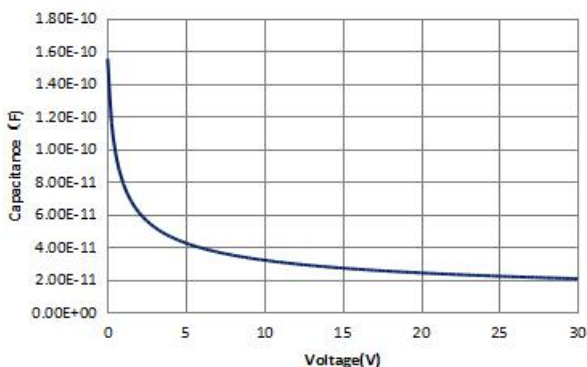
## Relative Short Circuit

Current vs. Illumination

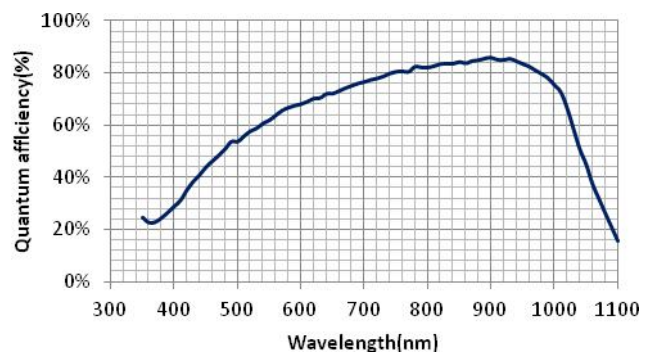


## Relative Junction Capacitance

VS. Voltage



## Quantum efficiency



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